

Randall Feenstra

List of Publications by Year in descending order

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269
papers

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citations

16451

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283
all docs

283
docs citations

283
times ranked

9425
citing authors

#	ARTICLE	IF	CITATIONS
1	Tunneling spectroscopy of the Si(111)2 Å ⁻¹ surface. Surface Science, 1987, 181, 295-306.	1.9	606
2	Electronic Structure of the Si(111)2 Å ⁻¹ Surface by Scanning-Tunneling Microscopy. Physical Review Letters, 1986, 57, 2579-2582.	7.8	597
3	Atom-selective imaging of the GaAs(110) surface. Physical Review Letters, 1987, 58, 1192-1195.	7.8	596
4	Tunneling spectroscopy of the GaAs(110) surface. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1987, 5, 923.	1.6	395
5	Tunneling spectroscopy of the (110) surface of direct-gap III-V semiconductors. Physical Review B, 1994, 50, 4561-4570.	3.2	377
6	Reconstructions of the GaN(0001) Surface. Physical Review Letters, 1997, 79, 3934-3937.	7.8	331
7	Structure of GaN(0001): The laterally contracted Ga bilayer model. Physical Review B, 2000, 61, 9932-9935.	3.2	322
8	Determination of wurtzite GaN lattice polarity based on surface reconstruction. Applied Physics Letters, 1998, 72, 2114-2116.	3.3	305
9	Adatom Kinetics On and Below the Surface: The Existence of a New Diffusion Channel. Physical Review Letters, 2003, 90, 056101.	7.8	293
10	Real-space observation of $\sqrt{3}\times\sqrt{3}$ -bonded chains and surface disorder on Si(111)2 Å ⁻¹ . Physical Review Letters, 1986, 56, 608-611.	7.8	269
11	Geometric and electronic structure of antimony on the GaAs(110) surface studied by scanning tunneling microscopy. Physical Review B, 1989, 39, 7744-7753.	3.2	234
12	Reconstructions of GaN(0001) and (0001 $\bar{1}$) surfaces: Ga-rich metallic structures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1998, 16, 2242.	1.6	228
13	Asymmetries in dislocation densities, surface morphology, and strain of GaInAs/GaAs single heterolayers. Journal of Applied Physics, 1988, 64, 4843-4852.	2.5	208
14	Fermi-Level Pinning at the Sb/GaAs(110) Surface Studied by Scanning Tunneling Spectroscopy. Physical Review Letters, 1988, 61, 447-450.	7.8	202
15	Local state density and long-range screening of adsorbed oxygen atoms on the GaAs(110) surface. Physical Review Letters, 1987, 58, 1668-1671.	7.8	201
16	Preparation of atomically flat surfaces on silicon carbide using hydrogen etching. Journal of Electronic Materials, 1998, 27, 308-312.	2.2	188
17	Inversion of wurtzite GaN(0001) by exposure to magnesium. Applied Physics Letters, 1999, 75, 808-810.	3.3	187
18	Observation of bulk defects by scanning tunneling microscopy and spectroscopy: Arsenic antisite defects in GaAs. Physical Review Letters, 1993, 71, 1176-1179.	7.8	180

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19	Graphene Nucleation Density on Copper: Fundamental Role of Background Pressure. Journal of Physical Chemistry C, 2013, 117, 18919-18926.	3.1	179
20	Probing Critical Point Energies of Transition Metal Dichalcogenides: Surprising Indirect Gap of Single Layer WSe_2 . Nano Letters, 2015, 15, 6494-6500.	9.1	175
21	Realizing Large-Scale, Electronic-Grade Two-Dimensional Semiconductors. ACS Nano, 2018, 12, 965-975.	14.6	172
22	Influence of misfit dislocations on the surface morphology of $Si_{1-x}Ge_x$ films. Applied Physics Letters, 1995, 66, 724-726.	3.3	164
23	Ultrafast Transient Absorption Microscopy Studies of Carrier Dynamics in Epitaxial Graphene. Nano Letters, 2010, 10, 1308-1313.	9.1	164
24	Scanning tunneling spectroscopy. Surface Science, 1994, 299-300, 965-979.	1.9	163
25	Interface roughness and asymmetry in InAs/GaSb superlattices studied by scanning tunneling microscopy. Physical Review Letters, 1994, 72, 2749-2752.	7.8	157
26	Single-particle tunneling in doped graphene-insulator-graphene junctions. Journal of Applied Physics, 2012, 111, .	2.5	144
27	Surface diffusion and phase transition on the Ge(111) surface studied by scanning tunneling microscopy. Physical Review Letters, 1991, 66, 3257-3260.	7.8	132
28	Field effect in epitaxial graphene on a silicon carbide substrate. Applied Physics Letters, 2007, 90, 253507.	3.3	132
29	Spatially Resolved Mapping of Electrical Conductivity across Individual Domain (Grain) Boundaries in Graphene. ACS Nano, 2013, 7, 7956-7966.	14.6	124
30	Electrostatic potential for a hyperbolic probe tip near a semiconductor. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 2080.	1.6	123
31	Different Fermi-level pinning behavior on n- and p-type GaAs(001). Physical Review B, 1993, 48, 4612-4615.	3.2	120
32	Comprehensive structural and optical characterization of MBE grown $MoSe_2$ on graphite, CaF_2 and graphene. 2D Materials, 2015, 2, 024007.	4.4	120
33	GaN(0001) surface structures studied using scanning tunneling microscopy and first-principles total energy calculations. Surface Science, 1999, 423, 70-84.	1.9	118
34	Direct imaging of dopants in GaAs with cross-sectional scanning tunneling microscopy. Applied Physics Letters, 1993, 63, 2923-2925.	3.3	113
35	Low-Temperature Grown III-V Materials. Annual Review of Materials Research, 1995, 25, 547-600.	5.5	113
36	Electronic states of metal atoms on the GaAs(110) surface studied by scanning tunneling microscopy. Physical Review Letters, 1989, 63, 1412-1415.	7.8	111

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37	Scanning Tunneling Spectroscopy of Mott-Hubbard States on the 6H-SiC(0001) $\sqrt{3} \times \sqrt{3}$ Surface. <i>Physical Review Letters</i> , 1999, 82, 1000-1003.	7.8	108
38	Voltage-dependent scanning tunneling microscopy imaging of semiconductor surfaces. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1988, 6, 499-507.	2.1	107
39	Effects of GaAs substrate misorientation on strain relaxation in $\text{In}_x\text{Ga}_{1-x}\text{As}$ films and multilayers. <i>Journal of Applied Physics</i> , 1998, 83, 5137-5149.	2.5	102
40	Surface morphology of oxidized and ion-etched silicon by scanning tunneling microscopy. <i>Applied Physics Letters</i> , 1985, 47, 97-99.	3.3	97
41	Spontaneous Formation of Indium-Rich Nanostructures on InGaN(0001) Surfaces. <i>Physical Review Letters</i> , 2000, 85, 1902-1905.	7.8	95
42	SymFET: A Proposed Symmetric Graphene Tunneling Field-Effect Transistor. <i>IEEE Transactions on Electron Devices</i> , 2013, 60, 951-957.	3.0	93
43	Reconstruction of steps on the Si(111) $\sqrt{3} \times \sqrt{3}$ surface. <i>Physical Review Letters</i> , 1987, 59, 2173-2176.	7.8	91
44	Wurtzite GaN surface structures studied by scanning tunneling microscopy and reflection high energy electron diffraction. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1998, 16, 1641-1645.	2.1	91
45	Quantum-Confined Electronic States Arising from the Moiré Pattern of $\text{MoS}_2/\text{WSe}_2$ Heterobilayers. <i>Nano Letters</i> , 2018, 18, 1849-1855.	9.1	91
46	Surface structural and electronic properties of cleaved single crystals of $\text{Bi}_{2.15}\text{Sr}_{1.7}\text{CaCu}_2\text{O}_{8+\delta}$ compounds: A scanning tunneling microscopy study. <i>Physical Review B</i> , 1989, 40, 2682-2685.	3.2	90
47	Influence of tip-induced band bending on tunnelling spectra of semiconductor surfaces. <i>Nanotechnology</i> , 2007, 18, 044015.	2.6	89
48	Tunneling spectroscopy on compensating surface defects induced by Si doping of molecular-beam epitaxially grown GaAs(001). <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1992, 10, 1874.	1.6	88
49	Cross-sectional imaging and spectroscopy of GaAs doping superlattices by scanning tunneling microscopy. <i>Applied Physics Letters</i> , 1992, 61, 795-797.	3.3	88
50	Surface morphology of GaAs(110) by scanning tunneling microscopy. <i>Physical Review B</i> , 1985, 32, 1394-1396.	3.2	85
51	Structure of Cs on GaAs(110) as determined by scanning tunneling microscopy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1989, 7, 2868-2872.	2.1	83
52	Low-energy electron reflectivity from graphene. <i>Physical Review B</i> , 2013, 87, .	3.2	83
53	Relaxed $\text{Si}_{0.7}\text{Ge}_{0.3}$ buffer layers for high-mobility devices. <i>Applied Physics Letters</i> , 1995, 67, 2373-2375.	3.3	80
54	Band gap of the $\text{Ge}(111)c(2 \times 8)$ surface by scanning tunneling spectroscopy. <i>Physical Review B</i> , 2006, 73, .	3.2	78

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55	Comparison of graphene formation on C-face and Si-face SiC {0001} surfaces. Physical Review B, 2010, 82, .	3.2	76
56	Proximity-induced superconducting gap in the quantum spin Hall edge state of monolayer WTe ₂ . Nature Physics, 2020, 16, 526-530.	16.7	76
57	Scanning tunneling microscopy and spectroscopy of Bi-Sr-Ca-Cu-O 2:2:1:2 high-temperature superconductors. Physical Review B, 1991, 43, 7913-7922.	3.2	72
58	Surface structures and growth kinetics of InGaN(0001) grown by molecular beam epitaxy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2000, 18, 2284.	1.6	72
59	Scanning Tunneling Microscopy and Spectroscopy of Air Exposure Effects on Molecular Beam Epitaxy Grown WSe ₂ Monolayers and Bilayers. ACS Nano, 2016, 10, 4258-4267.	14.6	72
60	Formation of the 5 \times 5 reconstruction on cleaved Si(111) surfaces studied by scanning tunneling microscopy. Physical Review B, 1990, 42, 5391-5394.	3.2	70
61	Reconstructions of the AlN(0001) surface. Physical Review B, 2003, 68, .	3.2	70
62	Kinetics of the Si(111)2 \times 1 \times 5 and 7 \times 7 transformation studied by scanning tunneling microscopy. Surface Science, 1991, 243, 151-165.	1.9	69
63	Band gap of the Ge(111)2 \times 1 and Si(111)2 \times 1 surfaces by scanning tunneling spectroscopy. Physical Review B, 1991, 44, 13791-13794.	3.2	68
64	Cross-sectional scanning tunnelling microscopy of III-V semiconductor structures. Semiconductor Science and Technology, 1994, 9, 2157-2168.	2.0	67
65	Scanning tunneling microscope for low temperature, high magnetic field, and spatially resolved spectroscopy. Review of Scientific Instruments, 1987, 58, 1806-1810.	1.3	65
66	Recent developments in surface studies of GaN and AlN. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1174.	1.6	65
67	Scanning tunneling microscopy and spectroscopy of gold on the GaAs(110) surface. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1989, 7, 925.	1.6	64
68	Low-temperature tunneling spectroscopy of Ge(111)c(2 \times 8) surfaces. Physical Review B, 2005, 71, .	3.2	64
69	Scanning tunneling microscopy and spectroscopy of arsenic antisites in low temperature grown InGaAs. Applied Physics Letters, 1999, 74, 1439-1441.	3.3	63
70	Scattering from strain variations in high-mobility Si/SiGe heterostructures. Journal of Applied Physics, 1995, 78, 6091-6097.	2.5	62
71	Review of Structure of Bare and Adsorbate-Covered GaN(0001) Surfaces. MRS Internet Journal of Nitride Semiconductor Research, 2002, 7, 1.	1.0	62
72	Electronic and structural properties of a discommensurate monolayer system: GaAs(110)-(1 \times 1)Bi. Physical Review B, 1989, 39, 12925-12928.	3.2	61

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73	Surface Reconstruction during Molecular Beam Epitaxial Growth of GaN (0001). MRS Internet Journal of Nitride Semiconductor Research, 1998, 3, 1.	1.0	60
74	Role of Ga flux in dislocation reduction in GaN films grown on SiC(0001). Applied Physics Letters, 2001, 79, 3428-3430.	3.3	59
75	Imaging electronic surface states in real space on the Si(111) 2 \times 1 surface. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1987, 5, 838-841.	2.1	58
76	Adsorption and incorporation of silicon at GaN(0001) surfaces. Applied Physics Letters, 2002, 80, 2008-2010.	3.3	57
77	Epitaxial graphene homogeneity and quantum Hall effect in millimeter-scale devices. Carbon, 2017, 115, 229-236.	10.3	57
78	Scanning tunneling spectroscopy of oxygen adsorbates on the GaAs(110) surface. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1988, 6, 1472.	1.6	55
79	Roughness analysis of Si/SiGe heterostructures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 1608.	1.6	54
80	Carbon-assisted chemical vapor deposition of hexagonal boron nitride. 2D Materials, 2017, 4, 025117.	4.4	54
81	Structural and electronic properties of Bi/GaAs(110). Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1989, 7, 936.	1.6	53
82	Atomic-scale structure and electronic properties of GaN/GaAs superlattices. Applied Physics Letters, 1996, 69, 3698-3700.	3.3	52
83	Atomic-Scale Mapping of Thermoelectric Power on Graphene: Role of Defects and Boundaries. Nano Letters, 2013, 13, 3269-3273.	9.1	52
84	Scanning tunneling microscopy and spectroscopy of cleaved and annealed Ge(111) surfaces. Surface Science, 1991, 251-252, 401-407.	1.9	51
85	Comparison of electronic and mechanical contrast in scanning tunneling microscopy images of semiconductor heterojunctions. Physica B: Condensed Matter, 1999, 273-274, 796-802.	2.7	51
86	Growth of GaN on porous SiC and GaN substrates. Journal of Electronic Materials, 2003, 32, 855-860.	2.2	51
87	Low-temperature scanning tunneling spectroscopy of n-type GaAs(110) surfaces. Physical Review B, 2002, 66, .	3.2	50
88	Growth of nanoscale BaTiO ₃ /SrTiO ₃ superlattices by molecular-beam epitaxy. Journal of Materials Research, 2008, 23, 1417-1432.	2.6	49
89	Tunneling characteristics in chemical vapor deposited graphene-hexagonal boron nitride-graphene junctions. Applied Physics Letters, 2014, 104, .	3.3	49
90	Study of interface asymmetry in InAs-GaSb heterojunctions. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 1689.	1.6	47

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91	Structure of clean and arsenic-covered GaN(0001) surfaces. Journal of Crystal Growth, 2000, 209, 355-363.	1.5	47
92	One dimensional metallic edges in atomically thin WSe ₂ induced by air exposure. 2D Materials, 2018, 5, 025017.	4.4	47
93	Indium incorporation and surface segregation during InGaN growth by molecular beam epitaxy: experiment and theory. MRS Internet Journal of Nitride Semiconductor Research, 2001, 6, 1.	1.0	46
94	Morphology and effects of hydrogen etching of porous SiC. Journal of Applied Physics, 2002, 92, 4070-4074.	2.5	45
95	Arrangement of nitrogen atoms in GaAsN alloys determined by scanning tunneling microscopy. Applied Physics Letters, 2001, 78, 82-84.	3.3	44
96	Step formation on hydrogen-etched 6H-SiC{0001} surfaces. Surface Science, 2008, 602, 2936-2942.	1.9	44
97	Graphene formed on SiC under various environments: comparison of Si-face and C-face. Journal Physics D: Applied Physics, 2012, 45, 154001.	2.8	44
98	Oxidized GaN(0001) surfaces studied by scanning tunneling microscopy and spectroscopy and by first-principles theory. Journal of Vacuum Science & Technology B, 2006, 24, 2080.	1.3	43
99	Low-energy electron reflectivity of graphene on copper and other substrates. Physical Review B, 2013, 87, .	3.2	43
100	Local transport properties of thin bismuth films studied by scanning tunneling potentiometry. Physical Review B, 1996, 54, R5283-R5286.	3.2	42
101	Scanning tunneling microscopy and spectroscopy of thin metal films on the GaAs(110) surface. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1990, 8, 3379-3385.	2.1	41
102	Tunneling spectroscopy of midgap states induced by arsenic precipitates in low-temperature-grown GaAs. Applied Physics Letters, 1993, 63, 2528-2530.	3.3	40
103	Scanning tunneling microscopy of InAs/GaSb superlattices: Subbands, interface roughness, and interface asymmetry. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1994, 12, 2592.	1.6	40
104	Enhanced group-V intermixing in InGaAs/InP quantum wells studied by cross-sectional scanning tunneling microscopy. Applied Physics Letters, 1999, 75, 79-81.	3.3	39
105	Energy Gap Induced by Friedel Oscillations Manifested as Transport Asymmetry at Monolayer-Bilayer Graphene Boundaries. Physical Review X, 2014, 4, .	8.9	39
106	Large scale 2D/3D hybrids based on gallium nitride and transition metal dichalcogenides. Nanoscale, 2018, 10, 336-341.	5.6	38
107	Flat Bands and Mechanical Deformation Effects in the MoS ₂ -WSe ₂ Heterobilayers. ACS Nano, 2020, 14, 7564-7573.	14.6	38
108	Influence of surface states on tunneling spectra of n-type GaAs(110) surfaces. Physical Review B, 2009, 80, .	3.2	37

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109	Spatial variation of the observed energy gap in granular superconducting NbN films. Applied Physics Letters, 1987, 50, 1607-1609.	3.3	36
110	Studies of superconductors using a low-temperature, high-field scanning tunneling microscope. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1988, 6, 259-262.	2.1	36
111	Scanning tunneling microscopy and spectroscopy of the Si(111)5 \times 5 surface. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1991, 9, 716.	1.6	36
112	Theory of graphene-“insulator”-graphene tunnel junctions. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2014, 32, .	1.2	36
113	Morphology and surface reconstructions of GaN(11 $\bar{1}$,00) surfaces. Applied Physics Letters, 2003, 82, 1793-1795.	3.3	35
114	Temperature Dependence of Epitaxial Graphene Formation on SiC(0001). Journal of Electronic Materials, 2009, 38, 718-724.	2.2	35
115	Structure of oxygen adsorbed on the GaAs(110) surface studied using scanning tunneling microscopy. Physical Review B, 1987, 36, 7718-7721.	3.2	34
116	Properties of GaN epitaxial layers grown on 6H-SiC(0001) by plasma-assisted molecular beam epitaxy. Journal of Electronic Materials, 2001, 30, 162-169.	2.2	34
117	Morphology of graphene on SiC(0001 \bar{A}) surfaces. Applied Physics Letters, 2009, 95, 073101.	3.3	33
118	Scanning tunneling microscopy studies of Si(111) \hat{A} 2 \bar{A} -1 surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1986, 4, 1315-1319.	2.1	32
119	Temperature dependence of molecular beam epitaxy of GaN on SiC (0001). Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1999, 17, 1289-1293.	2.1	32
120	InGaAs/InP quantum well intermixing studied by cross-sectional scanning tunneling microscopy. Journal of Applied Physics, 2001, 89, 4815-4823.	2.5	32
121	Size, shape, composition, and electronic properties of InAs/GaAs quantum dots by scanning tunneling microscopy and spectroscopy. Journal of Applied Physics, 2010, 108, 114315.	2.5	32
122	Strain variations in InGaAsP/InGaP superlattices studied by scanning probe microscopy. Applied Physics Letters, 1998, 72, 1727-1729.	3.3	31
123	Dislocation density reduction in GaN using porous SiN interlayers. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 722-726.	1.8	31
124	Band offsets of InGaP \hat{A} GaAs heterojunctions by scanning tunneling spectroscopy. Journal of Applied Physics, 2008, 103, 073704.	2.5	31
125	Edge melting of the Ge(111) surface studied by scanning tunneling microscopy. Ultramicroscopy, 1992, 42-44, 33-40.	1.9	30
126	Scanning tunneling microscopy of the GaN(000 \hat{A} 1 \hat{A}) surface. Applied Physics A: Materials Science and Processing, 1998, 66, S947-S951.	2.3	30

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127	Transport limitations in tunneling spectroscopy of Ge(111)(2 \times 8) surfaces. Physical Review B, 2004, 69, .	3.2	30
128	Scanning tunneling microscopy of in situ cleaved and hydrogen passivated Si(110) cross-sectional surfaces. Surface Science, 1995, 328, 215-226.	1.9	28
129	Coexistence of Negatively and Positively Buckled Isomers on n-Doped Si(111) 2×2 Surface. Physical Review Letters, 2011, 106, 067601.	7.8	27
130	Interface structure of graphene on SiC(0001) studied by scanning tunneling microscopy. Physical Review B, 2012, 85, .	3.2	27
131	Properties of synthetic epitaxial graphene/molybdenum disulfide lateral heterostructures. Carbon, 2017, 125, 551-556.	10.3	27
132	Cross-sectional scanning tunneling microscopy of epitaxial GaAs structures. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1993, 11, 1502.	1.6	26
133	Efficacy of single and double SiNx interlayers on defect reduction in GaN overlayers grown by organometallic vapor-phase epitaxy. Journal of Applied Physics, 2005, 98, 123502.	2.5	26
134	Electronic states of oxidized GaN(0001) surfaces. Applied Physics Letters, 2006, 89, 171920.	3.3	26
135	Formation of epitaxial graphene on SiC(0001) using vacuum or argon environments. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2010, 28, C5C1-C5C7.	1.2	26
136	Buckling and band gap of the Ge(111) 2×2 surface studied by low-temperature scanning tunneling microscopy. Physical Review B, 2001, 64, .	3.2	25
137	Plasma-assisted molecular beam epitaxy of GaN on porous SiC substrates with varying porosity. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 1812.	1.6	25
138	Low-energy electron reflectivity from graphene: First-principles computations and approximate models. Ultramicroscopy, 2013, 130, 101-108.	1.9	24
139	Formation of metal/GaAs(110) interfaces studied by scanning tunneling microscopy. Applied Surface Science, 1992, 56-58, 104-116.	6.1	23
140	Distribution of nitrogen atoms in dilute GaAsN and InGaAsN alloys studied by scanning tunneling microscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1644.	1.6	23
141	Theory of resonant tunneling in bilayer-graphene/hexagonal-boron-nitride heterostructures. Applied Physics Letters, 2015, 106, .	3.3	23
142	Evidences of electrochemical graphene functionalization and substrate dependence by Raman and scanning tunneling spectroscopies. Journal of Applied Physics, 2012, 111, 114306.	2.5	22
143	Oxygen vacancies on SrO-terminated SrTiO ₃ studied by scanning tunneling spectroscopy. Physical Review B, 2015, 91, .	3.2	22
144	Vibrational modes of oxygen in GaP including nearest-neighbor interactions. Physical Review B, 1983, 28, 5793-5801.	3.2	21

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145	Optimized structural properties of wurtzite GaN on SiC(0001) grown by molecular beam epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2000, 18, 1915-1918.	2.1	21
146	Scanning tunneling potentiometry of semiconductor junctions. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1677.	1.6	21
147	A prospective: Quantitative scanning tunneling spectroscopy of semiconductor surfaces. Surface Science, 2009, 603, 2841-2844.	1.9	21
148	Tunneling spectroscopy of graphene and related reconstructions on SiC(0001). Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2009, 27, 1052-1057.	2.1	21
149	Tuning electronic transport in epitaxial graphene-based van der Waals heterostructures. Nanoscale, 2016, 8, 8947-8954.	5.6	21
150	Effect of interface composition and growth order on the mixed anion InAs/GaSb valence band offset. Applied Physics Letters, 1995, 66, 2981-2983.	3.3	20
151	Reconstructions of GaN and InGaN surfaces. Applied Surface Science, 2000, 166, 165-172.	6.1	20
152	Characterization of hexagonal boron nitride layers on nickel surfaces by low-energy electron microscopy. Surface Science, 2017, 659, 31-42.	1.9	20
153	Exciton capture cross sections of indium and boron impurities in silicon. Solid State Communications, 1980, 36, 1039-1045.	1.9	19
154	Isotope shifts for the P, Q, R lines in indium-doped silicon. Solid State Communications, 1983, 46, 321-324.	1.9	19
155	Morphological and compositional variations in strain-compensated InGaAsP/InGaP superlattices. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1997, 15, 1027.	1.6	19
156	In situ real-time studies of GaN growth on 6H-SiC(0001) by low-energy electron microscopy (LEEM). Journal of Crystal Growth, 1998, 189-190, 310-316.	1.5	19
157	Cross-sectional scanning tunneling microscopy and spectroscopy of InGaP/GaAs heterojunctions. Applied Physics Letters, 2004, 84, 227-229.	3.3	19
158	Real-Space Determination of Surface Structure by Scanning Tunneling Microscopy. Physica Scripta, 1987, T19A, 55-60.	2.5	18
159	Scanning tunneling microscopy and first-principles theory of the Sn/GaAs(110) surface. Physical Review B, 1989, 40, 10044-10047.	3.2	18
160	Growth of GaN on Porous Sic Substrates by Plasma-Assisted Molecular Beam Epitaxy. Materials Research Society Symposia Proceedings, 2002, 722, 131.	0.1	18
161	Defect Reactions in GaP: (Zn,O). Physical Review Letters, 1981, 47, 925-927.	7.8	17
162	Pinned and unpinned step dynamics on vicinal silver (110) surfaces. Physical Review B, 1993, 48, 8458-8461.	3.2	17

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163	SURFACE MORPHOLOGY OF GaN SURFACES DURING MOLECULAR BEAM EPITAXY. Surface Review and Letters, 2000, 07, 601-606.	1.1	17
164	Surface termination during GaN growth by metalorganic vapor phase epitaxy determined by ellipsometry. Journal of Applied Physics, 2003, 94, 6997-6999.	2.5	17
165	Structure and electronic spectroscopy of steps on GaAs(110) surfaces. Surface Science, 2012, 606, 28-33.	1.9	17
166	Formation of hexagonal boron nitride on graphene-covered copper surfaces. Journal of Materials Research, 2016, 31, 945-958.	2.6	17
167	Scanning tunneling microscopy of InAs/GaSb superlattices with various growth conditions. Superlattices and Microstructures, 1994, 15, 215.	3.1	16
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